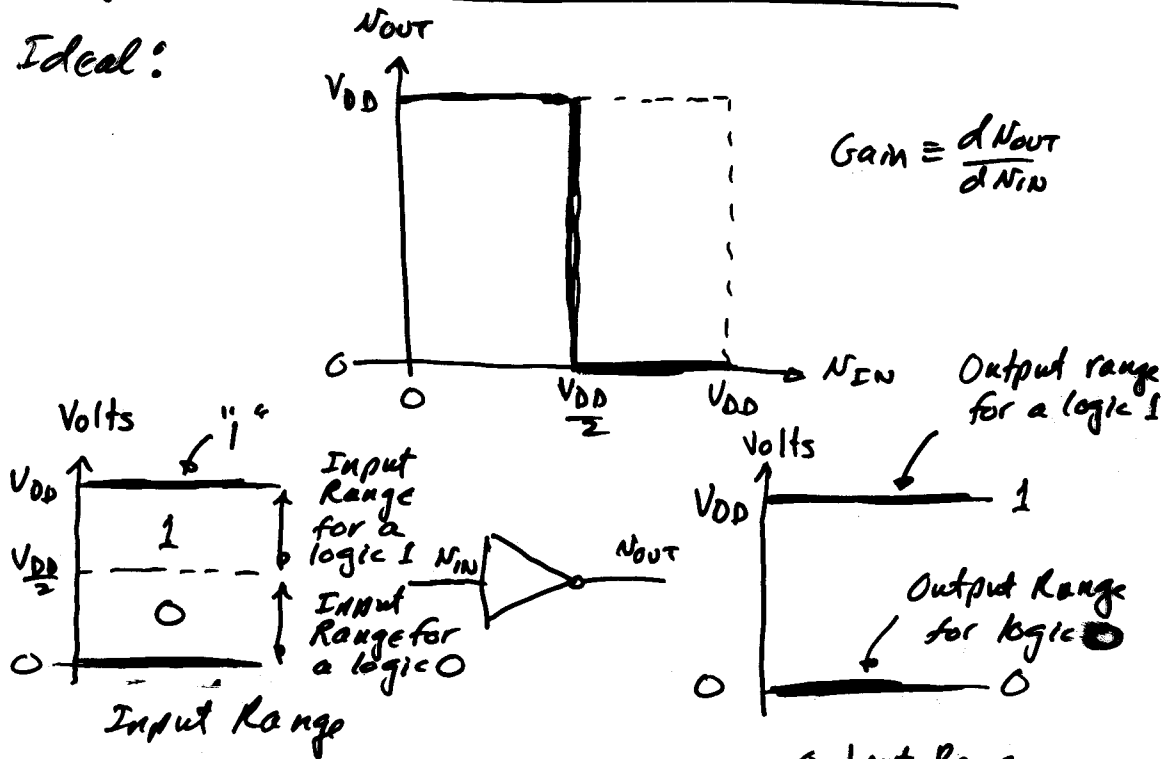


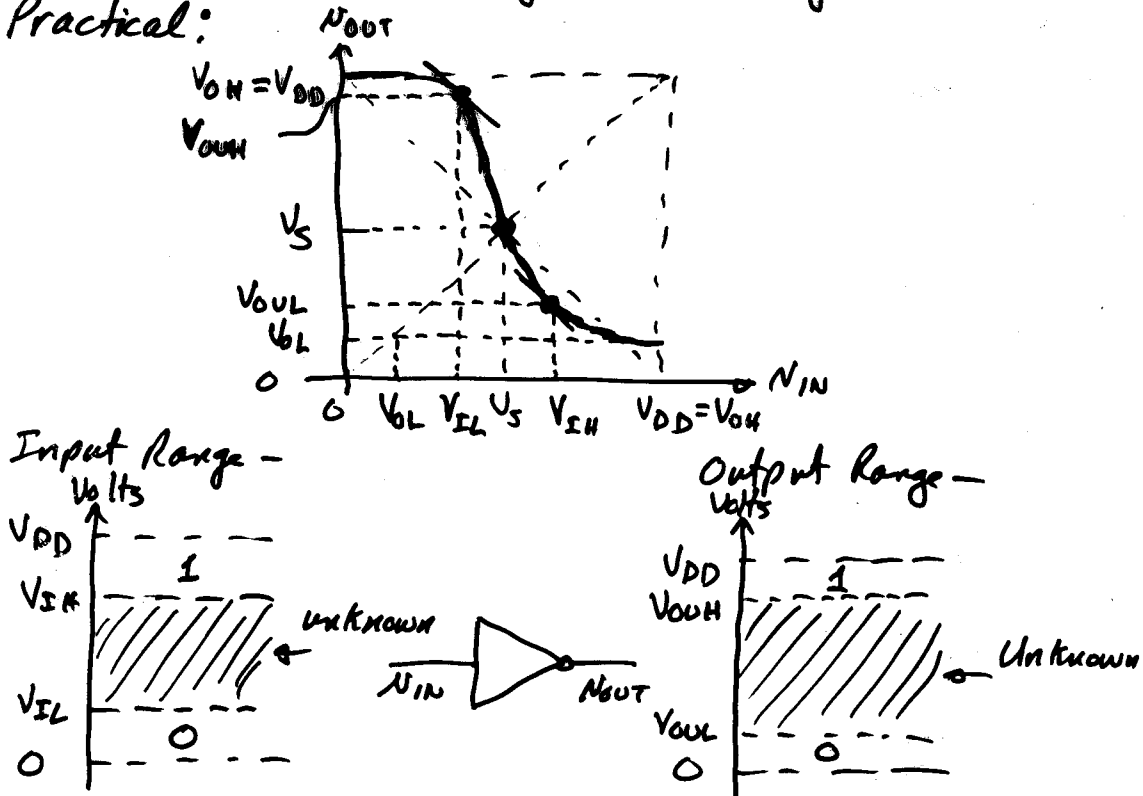
Voltage Transfer Characteristic of an Inverter

Ideal:



Output range < Input Range

Practical:



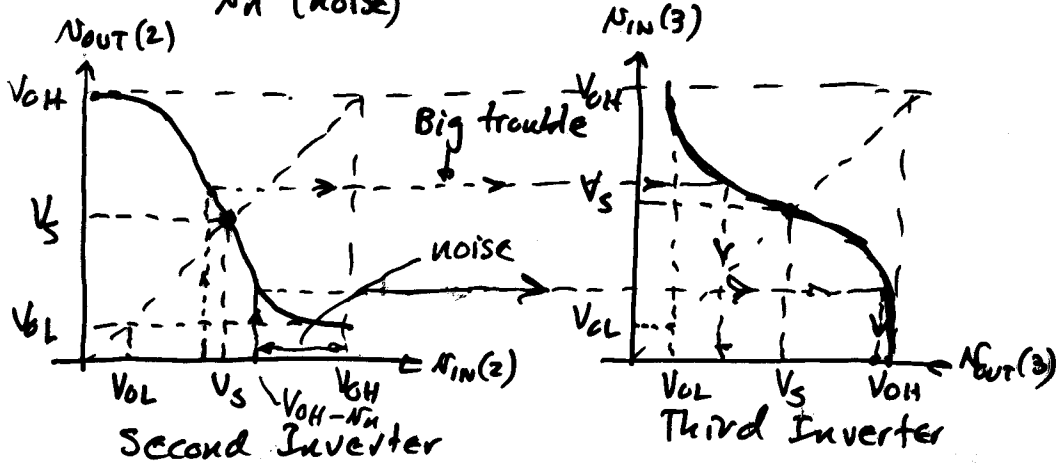
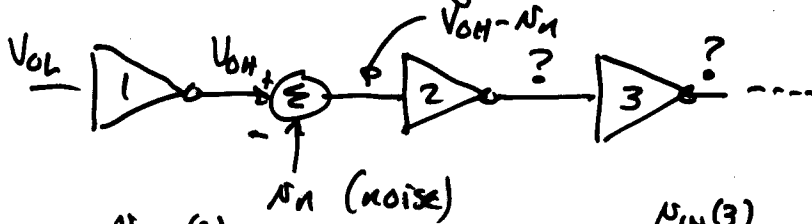
Noise Margin Definitions

Noise \equiv unwanted variations of voltages or currents at the logic nodes.

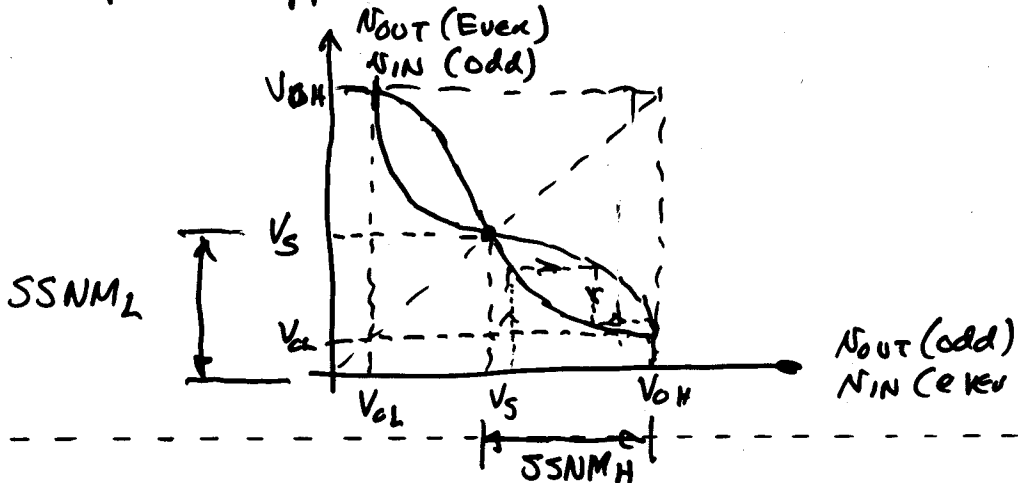
Noise Margin (NM) \equiv largest value of noise at the input that will be attenuated as it passes from input to output.

Single-Source Noise Margin

Consider the following



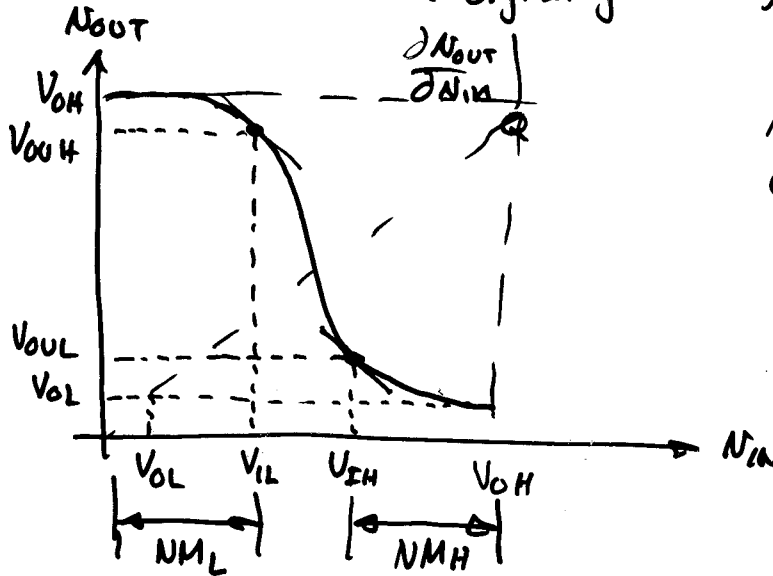
Graphical Approach for General Case -



Multiple-Source Noise Margin

Accounts for noise at all logic nodes.

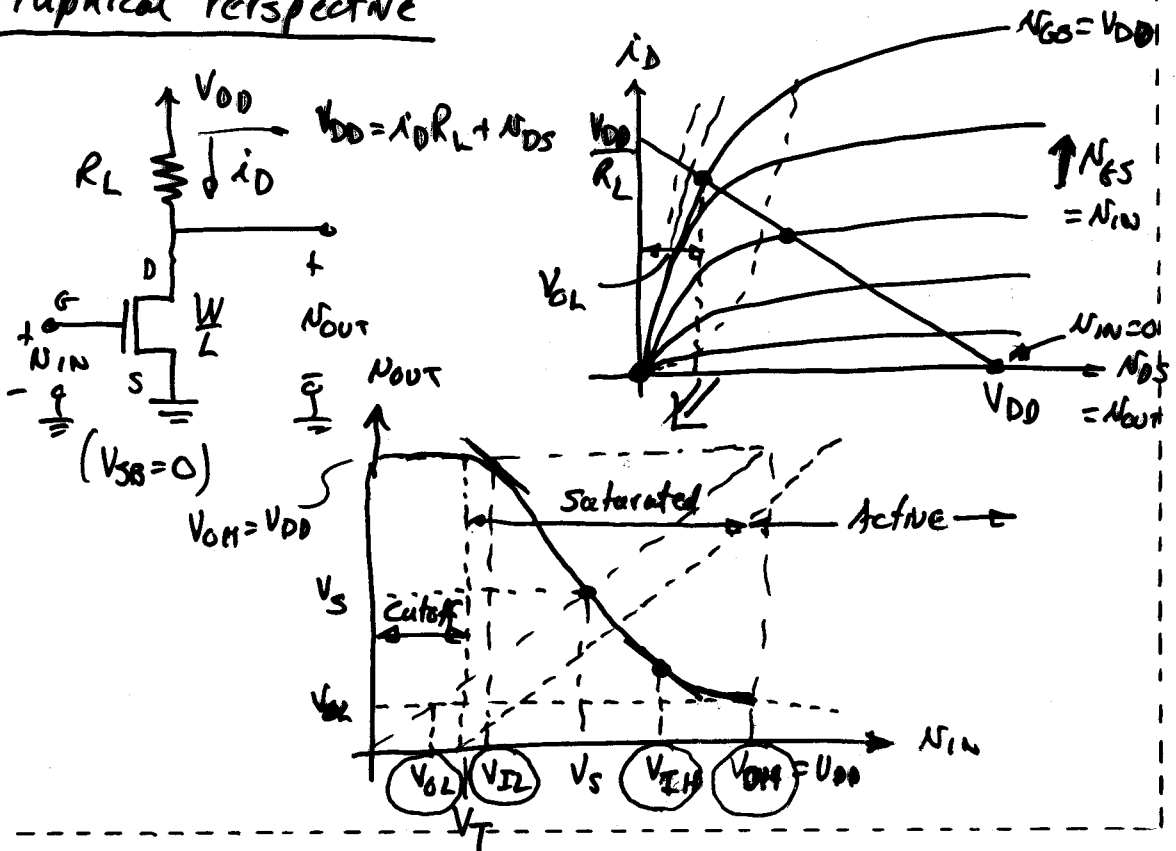
Principle: "If small-signal gain < 1 , noise can't grow."



Assumes that all logic gates have a gain magnitude greater than 1 at some point on the voltage transfer characteristics.

RESISTIVE LOAD INVERTER DESIGN

Graphical Perspective



Mathematical Perspective

1.) V_{OH} If $N_{in} < V_T$, then $V_{OH} = V_{DD}$

2.) $V_{OL} = ?$ Assume that the MOSFET is in the linear region

$$\therefore I_{RL} = I_{DS}(\text{linear}) \quad \begin{cases} V_{GS} = V_{OH} \\ V_{DS} = V_{OL} \end{cases}$$

$$\frac{V_{DD} - V_{OL}}{R_L} = \frac{1}{2} \frac{W_n}{L_n} \left(\frac{\mu_0 C_{ox}}{1 + \frac{V_{OL}}{E_{CLN}}} \right) [2(V_{OH} - V_T)V_{OL} - V_{OL}^2]$$

$$V_{OL} \approx \frac{V_{DD}}{1 + k R_L (V_{DD} - V_T)}$$